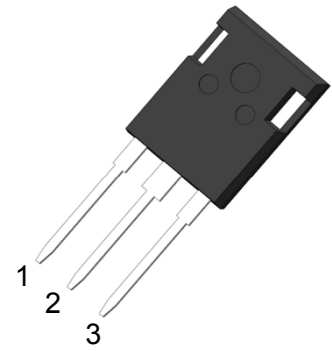


PRODUCT FEATURES

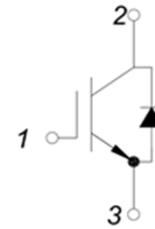
- ☐ 1200V IGBT chip in trench FS-technology
- ☐ Low switching losses
- ☐ $V_{CE(sat)}$ with positive temperature coefficient
- ☐ Fast switching and short tail current
- ☐ Free wheeling diodes with fast and soft reverse recovery



APPLICATIONS

- ☐ Motor control
- ☐ UPS/PFC
- ☐ General purpose inverters

1.Gate
2.Collector
3.Emitter



Type	V_{CES}	I_C	$V_{CE(sat)}$ $T_J=25^{\circ}C$	T_{Jmax}	Marking	Package
MM75G5U120BM	1200V	75A	1.7V	175°C	MM75G5U120BM	TO-247 PLUS

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MM75G5U120BM

ABSOLUTE MAXIMUM RATINGS($T_C=25^{\circ}\text{C}$ unless otherwise specified)

Symbol	Parameter/Test Conditions		Values	Unit
V_{CES}	Collector Emitter Voltage	$T_J=25^{\circ}\text{C}$	1200	V
V_{GES}	Gate Emitter Voltage		± 20	
	Transient Gate Emitter Voltage ($t_p \leq 10\mu\text{s}, D < 0.01$)		± 30	
I_C	DC Collector Current	$T_C=25^{\circ}\text{C}$	150	A
		$T_C=100^{\circ}\text{C}$	75	
I_{Cpuls}	Pulsed collector current, t_p limited by T_{Jmax}		300	
P_{tot}	Power Dissipation Per IGBT		535	W
V_{RRM}	Repetitive Reverse Voltage	$T_J=25^{\circ}\text{C}$	1200	V
I_F	Forward Current	$T_C=25^{\circ}\text{C}$	150	A
		$T_C=100^{\circ}\text{C}$	75	
I_{Fpuls}	Diode pulsed current, t_p limited by T_{Jmax}		300	
T_{Jmax}	Max. Junction Temperature		175	$^{\circ}\text{C}$
T_{Jop}	Operating Temperature		-40~175	
T_{stg}	Storage Temperature		-55~150	
T_{SLD}	Wave Soldering 1.6mm (0.063in.) from case for 10s		260	
Torque	to heatsink	Recommended (M3)	1.1	Nm
Weight			8	g

THERMAL RESISTANCE($T_C=25^{\circ}\text{C}$ unless otherwise specified)

Symbol	Parameter/Test Conditions	Min.	Typ.	Max.	Unit
R_{thJC}	Junction to Case Thermal Resistance (IGBT)			0.28	K /W
R_{thJCD}	Junction to Case Thermal Resistance (Diode)			0.49	
R_{thJA}	Junction to Ambient Thermal Resistance			40	

MM75G5U120BM

IGBT

ELECTRICAL CHARACTERISTICS ($T_C = 25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter/Test Conditions			Min.	Typ.	Max.	Unit
V _{GE(th)}	Gate Emitter Threshold Voltage	V _{CE} =V _{GE} , I _C =3.0mA		4.9	5.9	6.9	V
V _{CE(sat)}	Collector Emitter Saturation Voltage	I _C =75A, V _{GE} =15V, T _J =25°C			1.7	2.0	
		I _C =75A, V _{GE} =15V, T _J =125°C			2.05		
		I _C =75A, V _{GE} =15V, T _J =150°C			2.15		
I _{CES}	Collector Leakage Current	V _{CE} =1200V, V _{GE} =0V, T _J =25°C				100	μA
		V _{CE} =1200V, V _{GE} =0V, T _J =150°C				5	mA
I _{GES}	Gate Leakage Current	V _{CE} =0V,V _{GE} =±20V, T _J =25°C		-200		200	nA
g _{fs}	Transconductance	V _{CE} =20V, I _C =75A, T _J =25°C			90		S
Q _G	Gate Charge	V _{CE} =600V, I _C =75A , V _{GE} =15V			0.25		μC
C _{ies}	Input Capacitance	V _{CE} =25V, V _{GE} =0V, f =1MHz			6810		pF
C _{oes}	Output Capacitance				280		
C _{res}	Reverse Transfer Capacitance				49		
t _{d(on)}	Turn on Delay Time	V _{CC} =600V,I _C =75A R _G =10Ω, V _{GE} =15V, Inductive Load	T _J =25°C		56		ns
			T _J =125°C		54		ns
			T _J =150°C		54		ns
t _r	Rise Time		T _J =25°C		50		ns
			T _J =125°C		50		ns
			T _J =150°C		50		ns
t _{d(off)}	Turn off Delay Time		T _J =25°C		200		ns
			T _J =125°C		215		ns
			T _J =150°C		230		ns
t _f	Fall Time	T _J =25°C		110		ns	
		T _J =125°C		152		ns	
		T _J =150°C		170		ns	
E _{on}	Turn on Energy	V _{CC} =600V,I _C =75A R _G =10Ω, V _{GE} =15V, Inductive Load	T _J =125°C		6.9		mJ
			T _J =150°C		7.6		mJ
E _{off}	Turn off Energy		T _J =125°C		3.5		mJ
			T _J =150°C		3.8		mJ

Anti-Parallel Diode

ELECTRICAL CHARACTERISTICS ($T_C = 25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter/Test Conditions		Min.	Typ.	Max.	Unit
V_F	Forward Voltage	$I_F=75\text{A}, V_{GE}=0\text{V}, T_J=25^\circ\text{C}$		2	2.5	V
		$I_F=75\text{A}, V_{GE}=0\text{V}, T_J=125^\circ\text{C}$		1.75		
		$I_F=75\text{A}, V_{GE}=0\text{V}, T_J=150^\circ\text{C}$		1.7		
t_{rr}	Reverse Recovery Time	$I_F=75\text{A}, V_R=600\text{V}$ $dI_F/dt=-730\text{A}/\mu\text{s}$ $T_J=150^\circ\text{C}$		670		ns
I_{RRM}	Max. Reverse Recovery Current			42		A
Q_{RR}	Reverse Recovery Charge			13.4		μC
E_{rec}	Reverse Recovery Energy			5.8		mJ

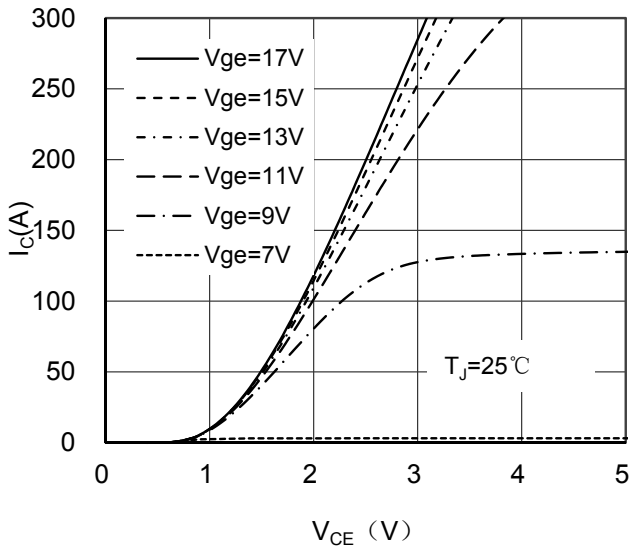


Figure 1. Typical Output Characteristics

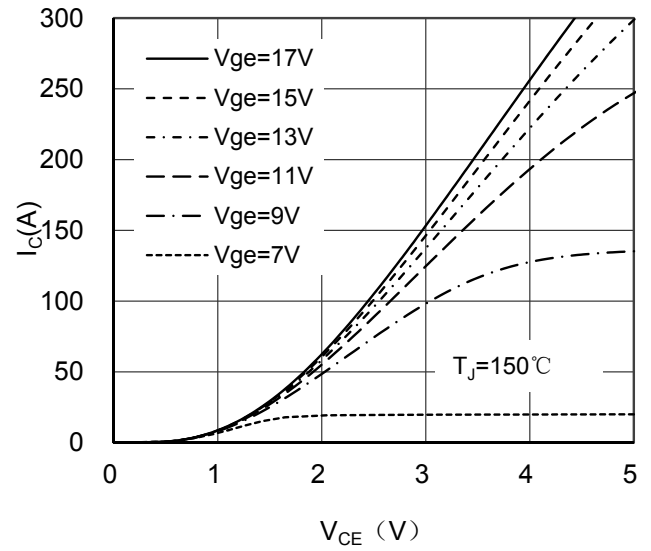


Figure 2. Typical Output Characteristics

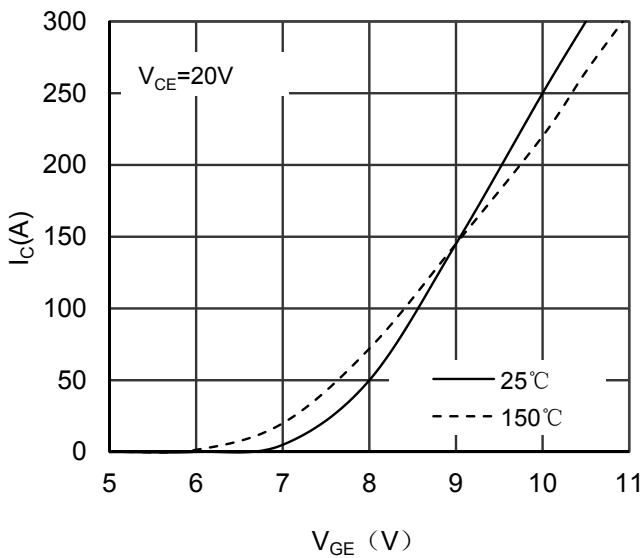


Figure 3. Typical Transfer characteristics

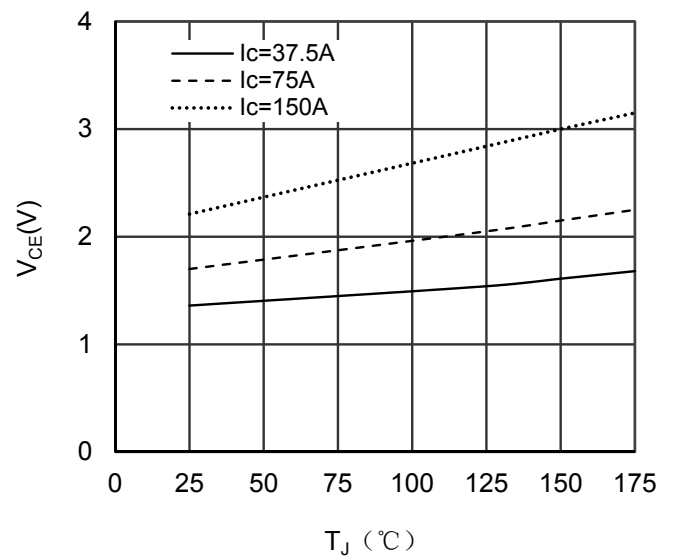


Figure 4. Collector-Emitter Voltage vs Junction temperature

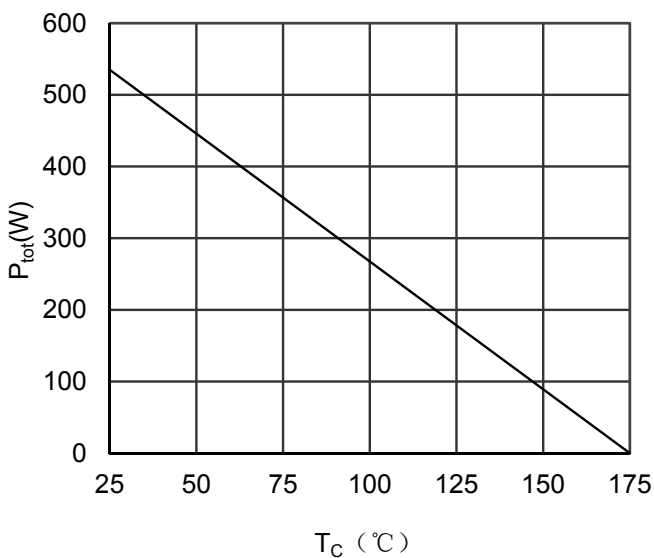


Figure 5. Power Dissipation vs Case temperature

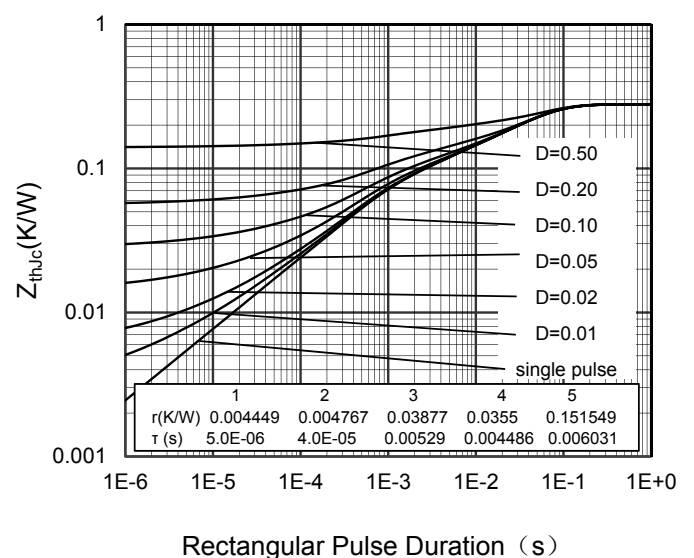


Figure 6. IGBT Transient Thermal Impedance

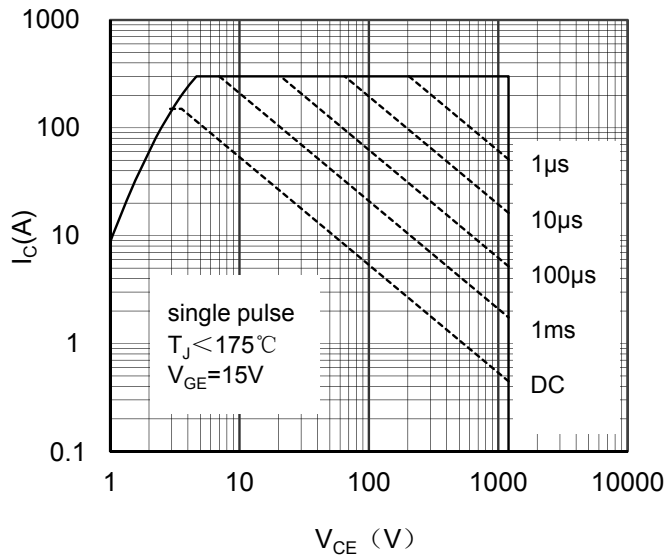


Figure 7. Forward Biased Safe Operating Area

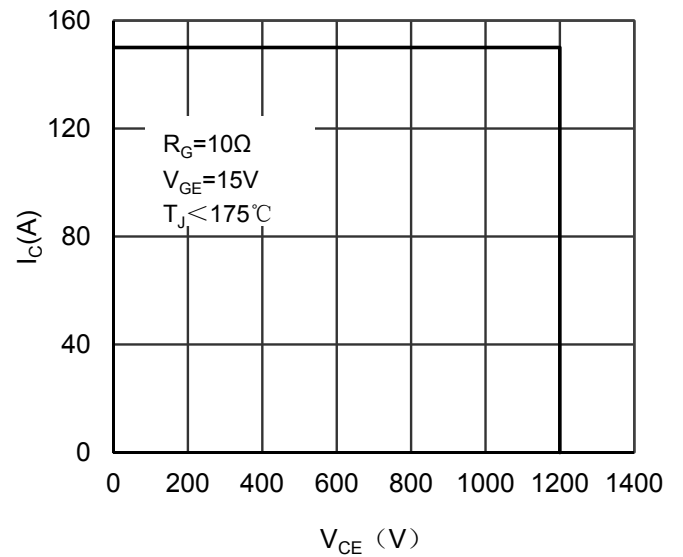


Figure 8. Reverse Biased Safe Operating Area

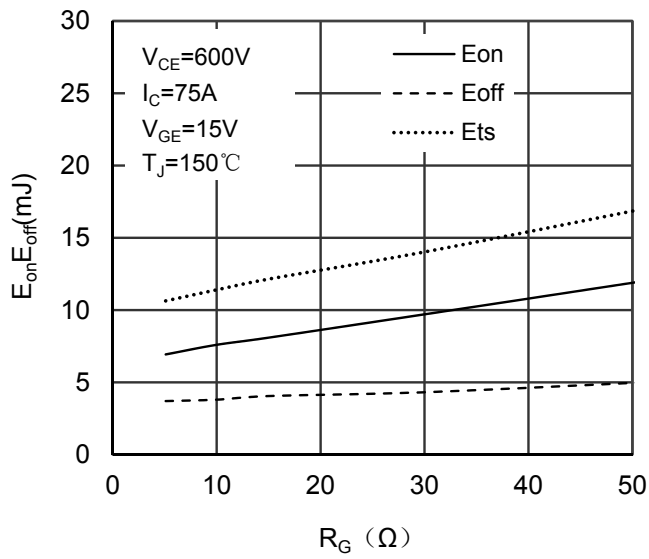


Figure 9. Switching Energy vs Gate Resistor

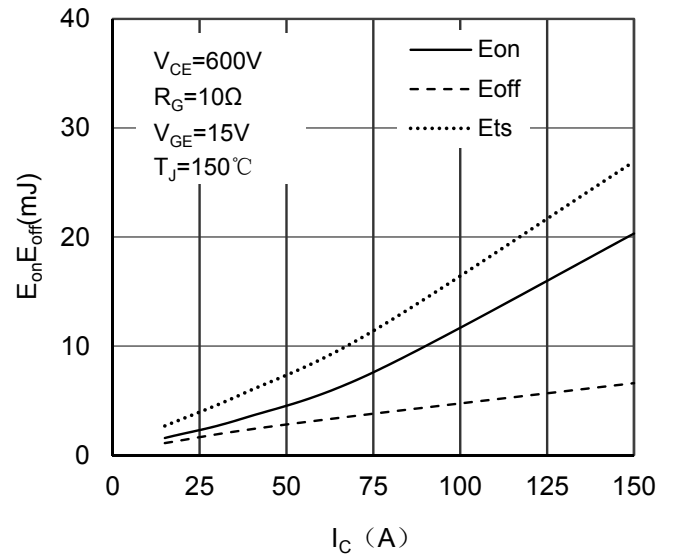


Figure 10. Switching Energy vs Collector Current

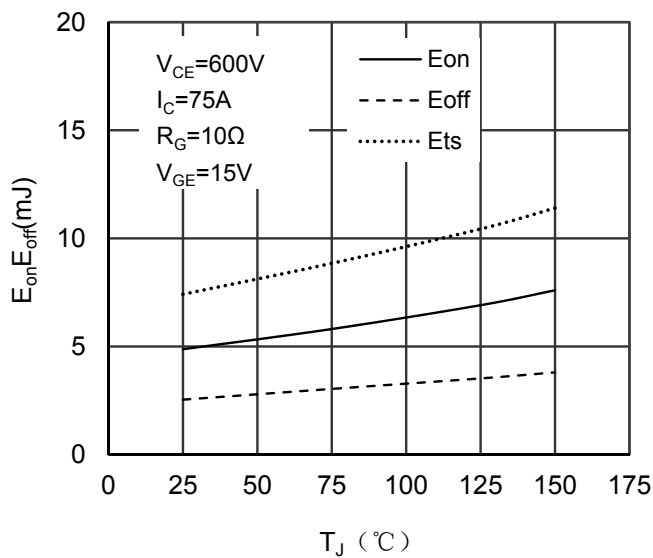


Figure 11. Switching Energy vs Junction temperature

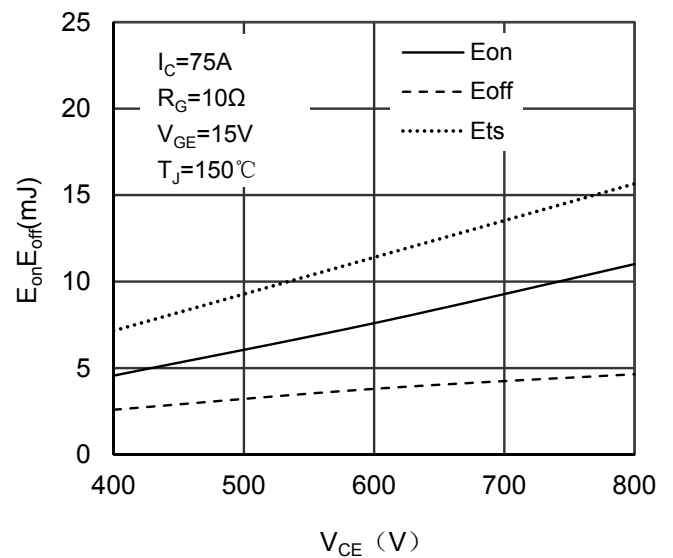


Figure 12. Switching Energy vs Collector-Emitter Voltage

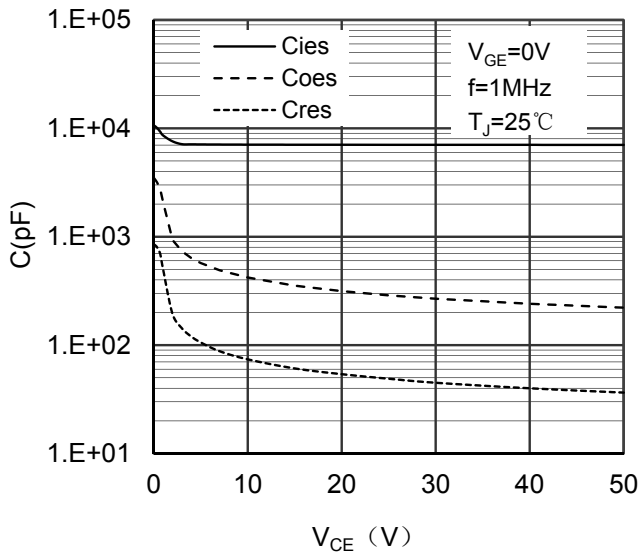


Figure 13. Typical capacitance

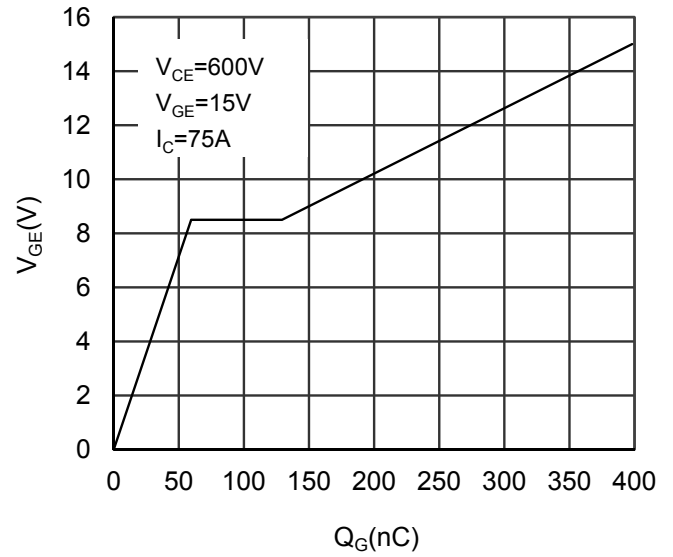


Figure 14. Typical Gate Charge

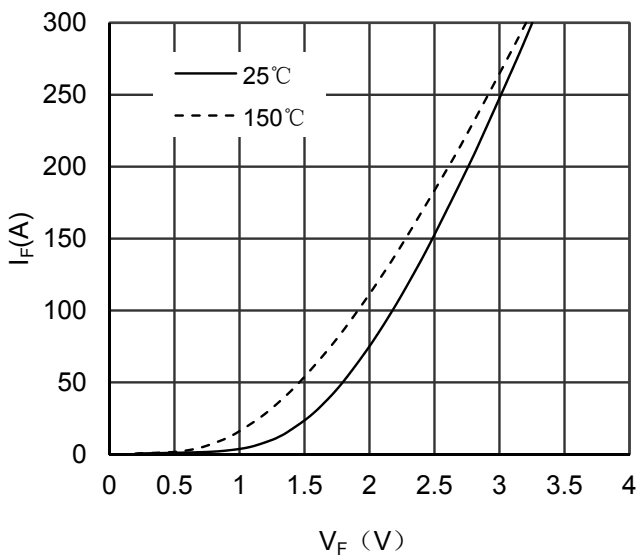


Figure 15. Diode Forward Characteristics

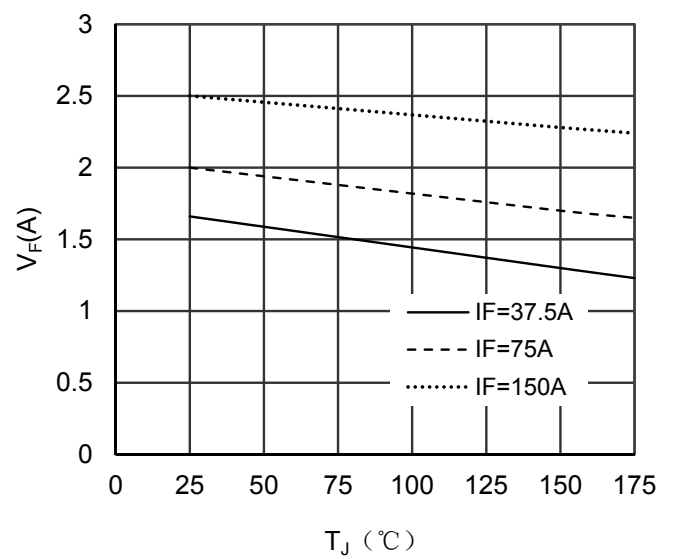


Figure 16. Forward Voltage vs Junction temperature

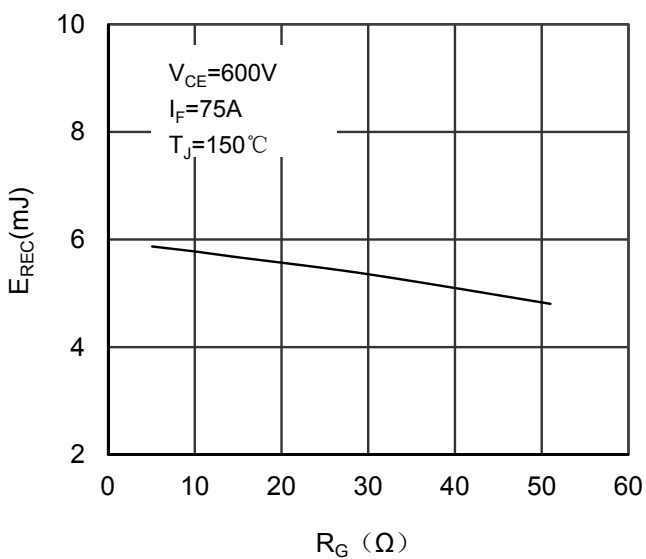


Figure 17. Switching Energy vs Gate Resistor

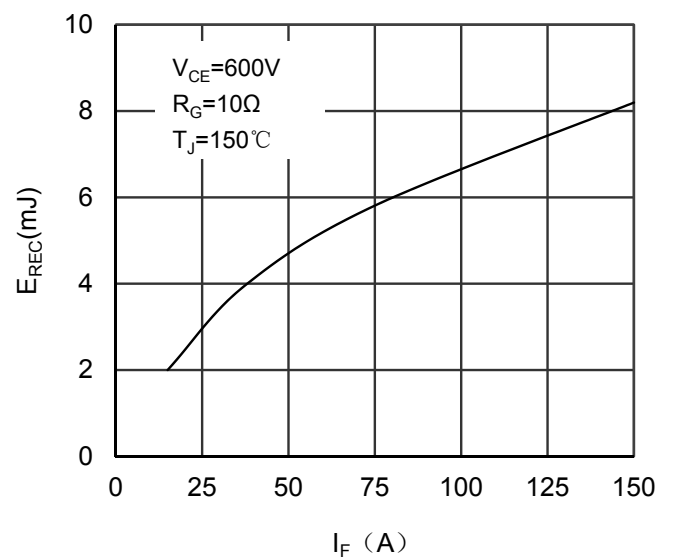


Figure 18. Switching Energy vs Forward Current

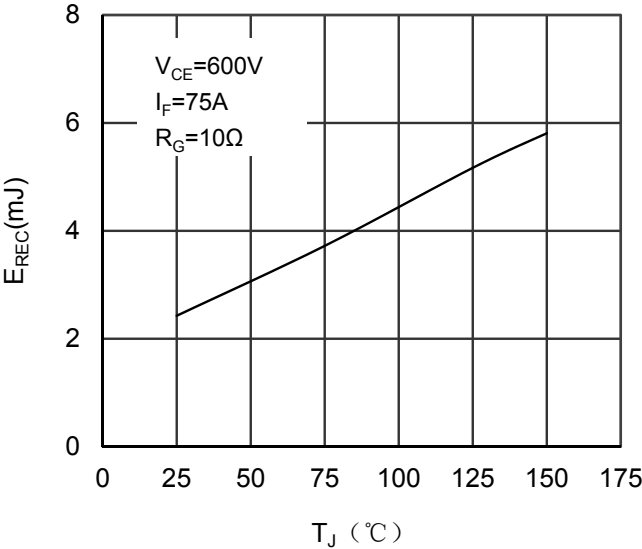


Figure 19. Switching Energy vs Junction temperature

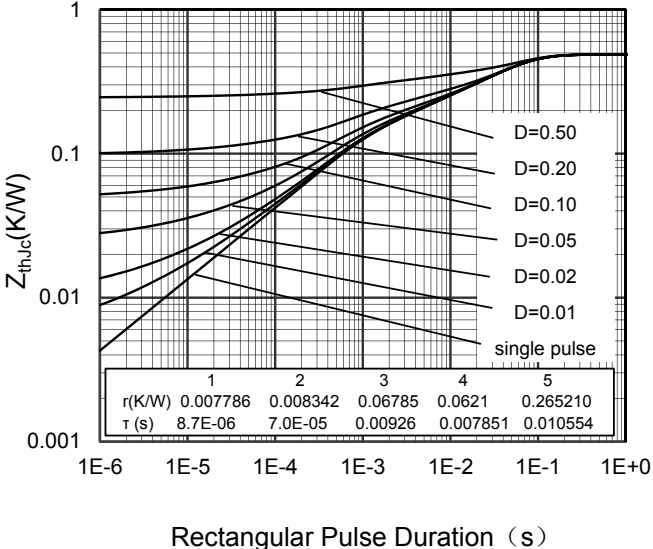
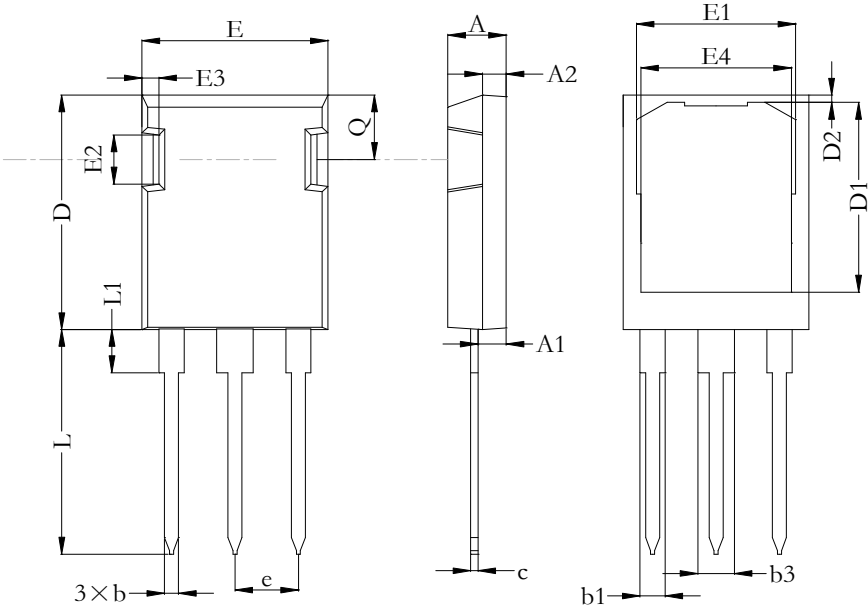


Figure 20. Diode Transient Thermal Impedance



Symbol	Min	Nom	Max
A	4.83	5.02	5.21
A1	2.29	2.42	2.54
A2	1.91	2.04	2.16
b	1.07	1.20	1.33
b1	1.91	2.16	2.41
b3	2.87	3.13	3.38
c	0.55	0.62	0.68
e	5.44BSC		
D	20.80	20.95	21.10
D1	16.25	16.95	17.65
D2	0.50	0.65	0.80
E	15.75	15.94	16.13
E1	13.10	13.63	14.15
E2	3.68	4.39	5.10
E3	1.00	1.45	1.90
E4	12.38	12.91	13.43
L	19.81	20.07	20.32
L1	3.70	3.85	4.00
Q	5.49	5.75	6.00

单位： mm

Figure 21. Package Outline